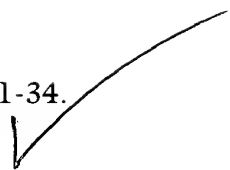


Cancel claims 1-34.



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35. (Amended) A method of fabricating a flip chip semiconductor die,  
comprising depositing a solder material on each of a plurality of connection sites, wherein  
the diameter of each said deposited solder material is about 10 microns or less.

A1

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44. (New) The method of claim 35, wherein a pitch between respective ones of  
said deposited solder material is less than about 100 microns.

A2

45. (New) The method of claim 44, wherein a pitch between respective ones of  
said deposited solder material is less than about 25 microns.

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